Silicon NPN Power Transistors 2SC508

DESCRIPTION

·With TO-66 package

·High collector-base breakdown voltage

:V_{CBO}=180V(min)

APPLICATIONS

·For power switching and TV horizontal output applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	180	V
V_{CEO}	Collector-emitter voltage	Open base	60	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		4	A
P_D	Total power dissipation	T_C=25?	25	W
T_j	Junction temperature		150	?
T_{stg}	Storage temperature		-65~200	?

CHARACTERISTICS

Tj=25? unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=30mA; I_B=0	60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA; I_E=0	180			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA; I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4A; I_B=0.4 A			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4A; I_B=0.4 A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=180V;I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			100	μA
h_{FE}	DC current gain	I_C=4A ; V_{CE}=5V	20			

PACKAGE OUTLINE

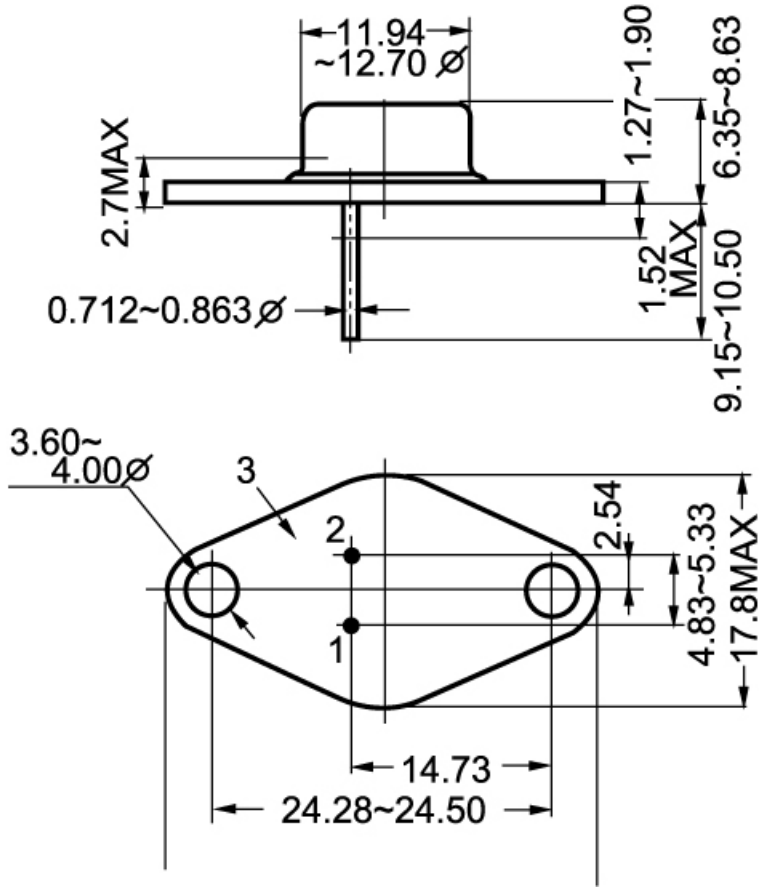

Fig.2 outline dimensions